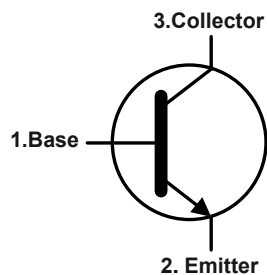


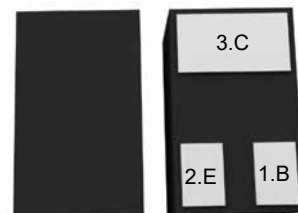
Features

- For Switching and AF Amplifier Applications.

Equivalent Circuit

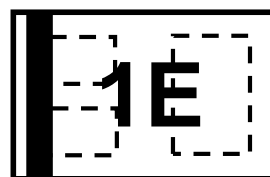


DFN1x0.6-3L



1.Base 2.Emitter 3.Collector

Marking Code :



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Maximum Power Dissipation	P_D	250	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

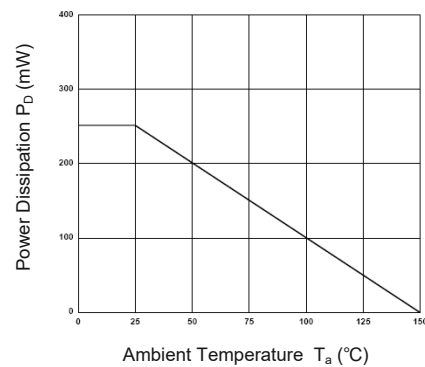
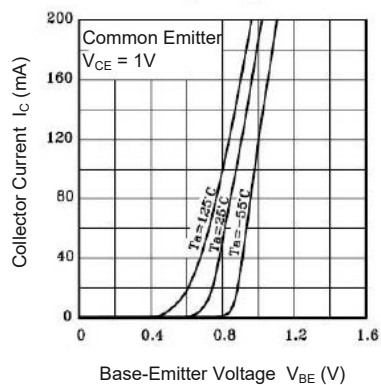
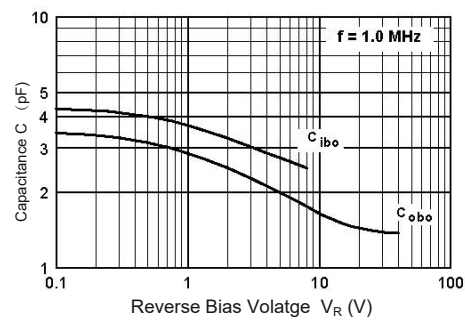
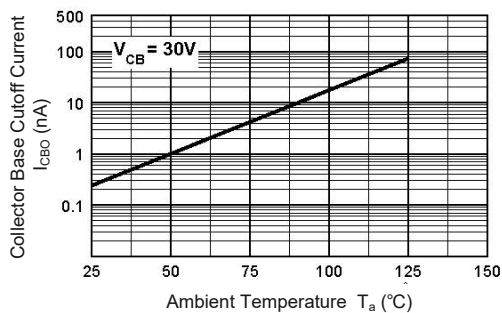
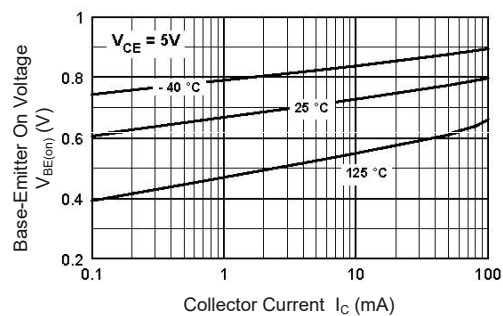
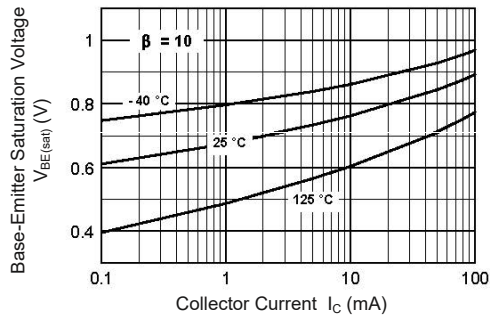
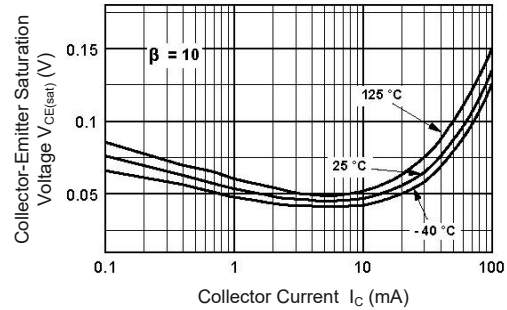
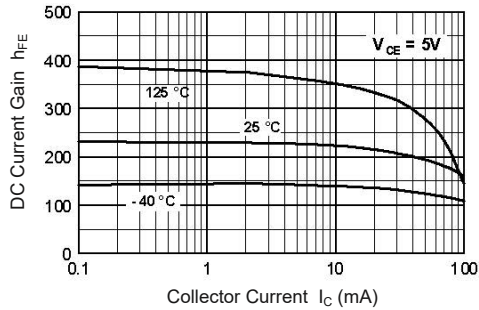


Electrical Characteristics (T_A=25°C)

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at V _{CE} = 1 V, I _C = 0.1 mA at V _{CE} = 1 V, I _C = 1 mA at V _{CE} = 1 V, I _C = 10 mA at V _{CE} = 1 V, I _C = 50 mA at V _{CE} = 1 V, I _C = 100 mA	H _{FE}	40 70 100 60 30	-- -- 300 -- --	--
Collector Base Cutoff Current at V _{CB} = 30V	I _{CBO}	--	50	nA
Emitter Base Cutoff Current at V _{EB} = 6 V	I _{EBO}	--	50	nA
Collector Base Breakdown Voltage at I _C = 10 μA	V _{(BR)CBO}	60	--	V
Collector Emitter Breakdown Voltage at I _C = 1 mA	V _{(BR)CEO}	40	--	V
Emitter Base Breakdown Voltage at I _E = 10 μA	V _{(BR)EBO}	6	--	V
Collector Emitter Saturation Voltage at I _C = 10 mA, I _B = 1 mA at I _C = 50 mA, I _B = 5 mA	V _{CE(sat)}	-- --	0.2 0.3	V
Base Emitter Saturation Voltage at I _C = 10 mA, I _B = 1 mA at I _C = 50 mA, I _B = 5 mA	V _{BE(sat)}	0.65 --	0.85 0.95	V
Transition Frequency at V _{CE} = 20 V, I _C = 10 mA, f = 100 MHz	F _T	300	--	MHz
Output Capacitance at V _{CB} = 5 V, I _E = 0, f = 1 MHz	C _{ob}	--	4	pF



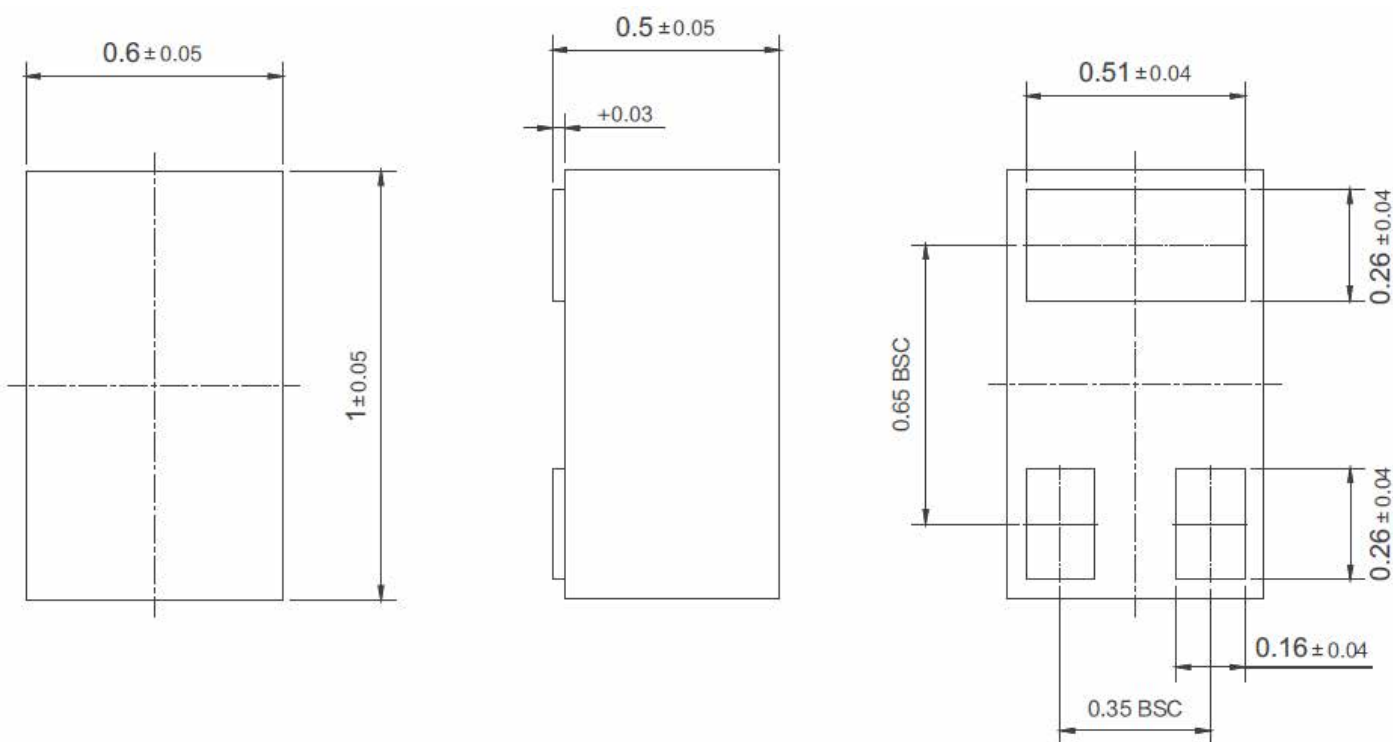
Typical Characteristic Curves



Package Outline

DFN1x0.6-3L-0009

Dimensions in mm



Ordering Information

Device	Package	Shipping
MMBT3904DC	DFN1x0.6-3L	10,000PCS/Reel&7inches